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ITO film, Deposited at 200 C with O_2 Flow-rate of 35 sccm using E-beam#2

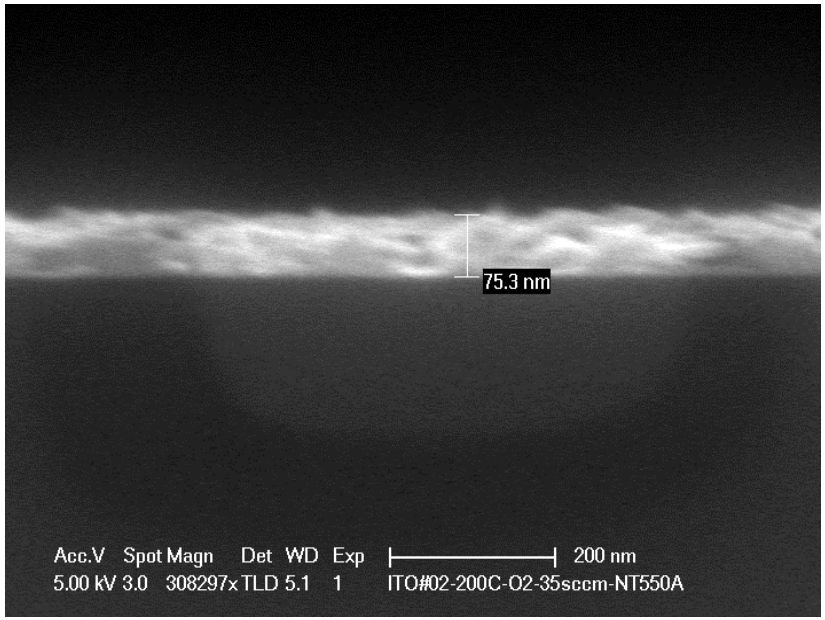
Samples: Si, SiO2/Si, and glass.

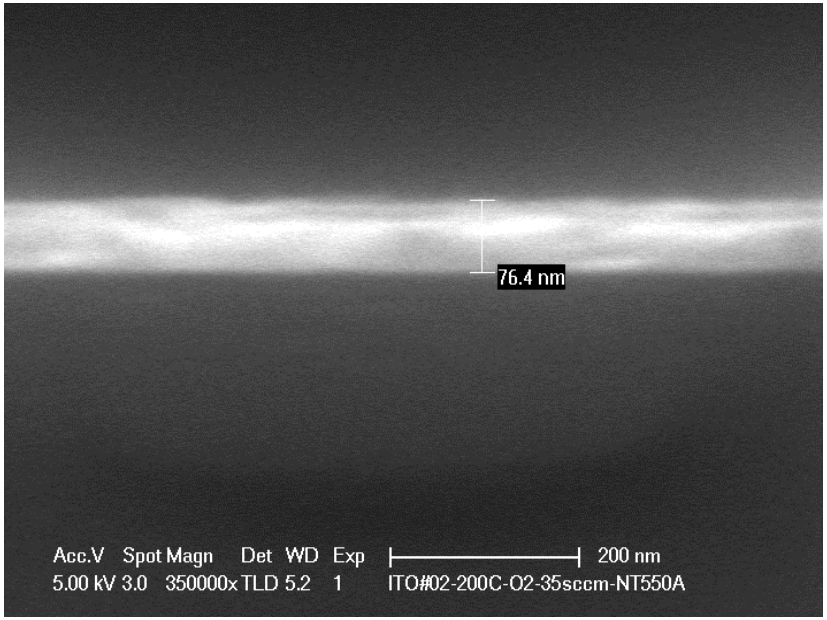
Tool: E-beam#2: tooling factor=110, rate=1 Å/s, chuck temperature =200^{o}C (480), Base pressure=3.57e-6 Torr, working pressure=3.6 e-4 Torr.

Results:

1) Resistivity=9.51x10^{-4} Ωcm.

2) Film Profile





3) Transmission Spectrum